

# MBRB2535CTLG, NRVBB2535CTLG

Preferred Device

## SWITCHMODE Power Rectifier

### D<sup>2</sup>PAK Surface Mount Power Package

The D<sup>2</sup>PAK Power Rectifier employs the Schottky Barrier principle in a large metal-to-silicon power diode. State-of-the-art geometry features epitaxial construction with oxide passivation and metal overlay contact. Ideally suited for use in low voltage, high frequency switching power supplies, free wheeling diodes, and polarity protection diodes. These state-of-the-art devices have the following features:

#### Features

- Center-Tap Configuration
- Guardring for Stress Protection
- Low Forward Voltage
- 125°C Operating Junction Temperature
- Epoxy Meets UL 94, V-0 @ 0.125 in
- Short Heatsink Tab Manufactured – Not Sheared
- Similar in Size to the Industry Standard TO-220 Package
- AEC-Q101 Qualified and PPAP Capable
- NRVBB Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements
- All Packages are Pb-Free\*

#### Mechanical Characteristics

- Case: Epoxy, Molded, Epoxy Meets UL 94, V-0
- Weight: 1.7 grams (approximately)
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead and Mounting Surface Temperature for Soldering Purposes: 260°C Max. for 10 Seconds
- Device Meets MSL1 Requirements
- ESD Ratings:
  - ◆ Machine Model = C (> 400 V)
  - ◆ Human Body Model = 3B (> 8000 V)

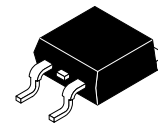
\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.



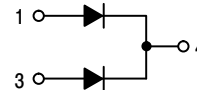
ON Semiconductor®

<http://onsemi.com>

### SCHOTTKY BARRIER RECTIFIER 25 AMPERES, 35 VOLTS



D<sup>2</sup>PAK  
CASE 418B  
STYLE 3



#### MARKING DIAGRAM



A = Assembly Location  
Y = Year  
WW = Work Week  
B2535L = Device Code  
G = Pb-Free Package  
AKA = Diode Polarity

#### ORDERING INFORMATION

Device	Package	Shipping†
MBRB2535CTLG	D <sup>2</sup> PAK (Pb-Free)	50 Units/Rail
NRVBB2535CTLG	D <sup>2</sup> PAK (Pb-Free)	50 Units/Rail
MBRB2535CTLT4G	D <sup>2</sup> PAK (Pb-Free)	800 / Tape & Reel
NRVBB2535CTLT4G	D <sup>2</sup> PAK (Pb-Free)	800 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

Preferred devices are recommended choices for future use and best overall value.

# MBRB2535CTLG, NRVBB2535CTLG

## MAXIMUM RATINGS (Per Leg)

Rating	Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	$V_{RRM}$ $V_{RWM}$ $V_R$	35	V
Average Rectified Forward Current, (Rated $V_R$ , $T_C = 110^\circ\text{C}$ )	$I_{F(AV)}$	12.5	A
Peak Repetitive Forward Current, (Rated $V_R$ , Square Wave, 20 kHz, $T_C = 90^\circ\text{C}$ )	$I_{FRM}$	25	A
Non-Repetitive Peak Surge Current (Surge Applied at Rated Load Conditions Halfwave, Single Phase, 60 Hz)	$I_{FSM}$	150	A
Peak Repetitive Reverse Surge Current (2.0 $\mu\text{s}$ , 1.0 kHz)	$I_{RRM}$	1.0	A
Storage Temperature Range	$T_{stg}$	-65 to +150	$^\circ\text{C}$
Operating Junction Temperature	$T_J$	-65 to +125	$^\circ\text{C}$
Voltage Rate of Change (Rated $V_R$ )	dv/dt	10,000	V/ $\mu\text{s}$

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

## THERMAL CHARACTERISTICS (Per Leg)

Characteristic	Symbol	Value	Unit
Thermal Resistance Junction-to-Case Junction-to-Ambient (Note 1)	$R_{\theta JC}$ $R_{\theta JA}$	1.0 84	$^\circ\text{C}/\text{W}$

1. When mounted using minimum recommended pad size on FR-4 board.

## ELECTRICAL CHARACTERISTICS (Per Leg)

Characteristic	Symbol	Value	Unit
Maximum Instantaneous Forward Voltage (Note 2) ( $i_F = 25\text{ A}$ , $T_J = 25^\circ\text{C}$ ) ( $i_F = 12.5\text{ A}$ , $T_J = 125^\circ\text{C}$ ) ( $i_F = 12.5\text{ A}$ , $T_J = 25^\circ\text{C}$ )	$v_F$	0.55 0.41 0.47	V
Maximum Instantaneous Reverse Current (Note 2) (Rated dc Voltage, $T_J = 125^\circ\text{C}$ ) (Rated dc Voltage, $T_J = 25^\circ\text{C}$ )	$I_R$	500 10	mA

2. Pulse Test: Pulse Width = 300  $\mu\text{s}$ , Duty Cycle  $\leq 2.0\%$ .

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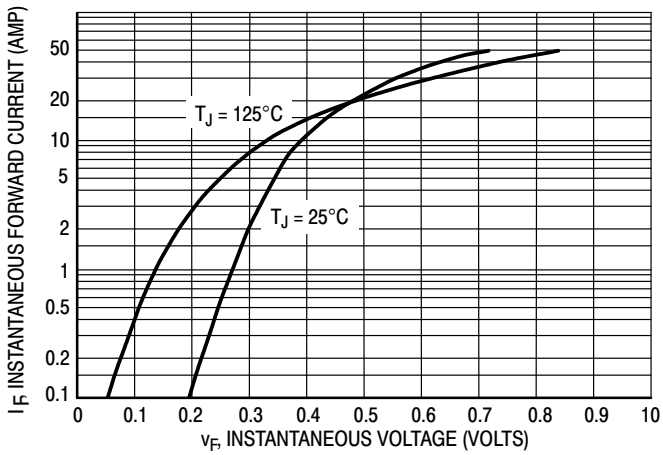


Figure 1. Typical Forward Voltage, Per Leg

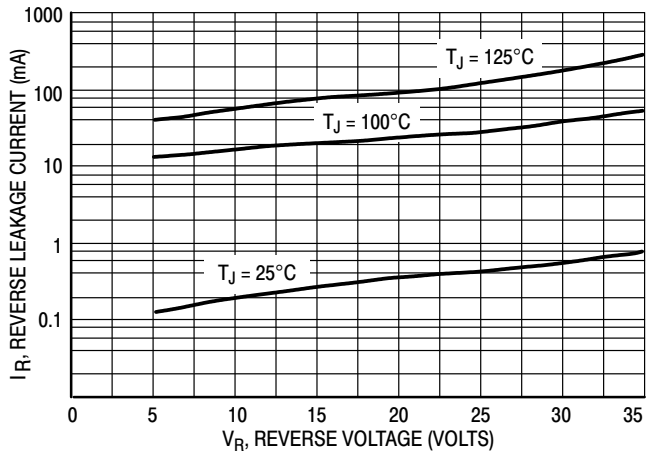


Figure 2. Typical Reverse Current, Per Leg

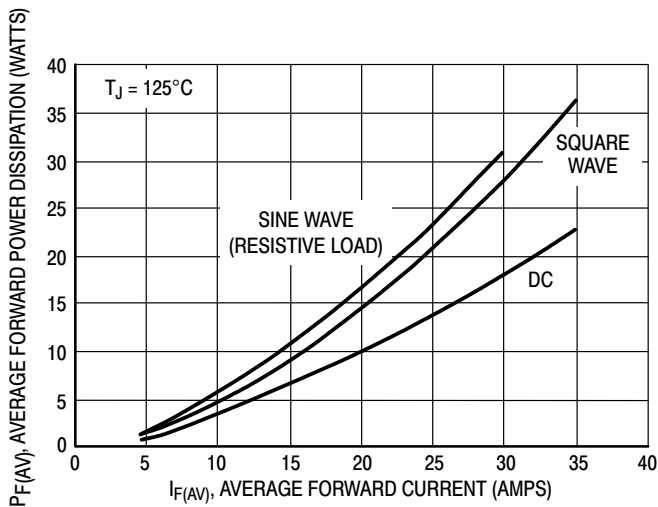


Figure 3. Typical Forward Power Dissipation

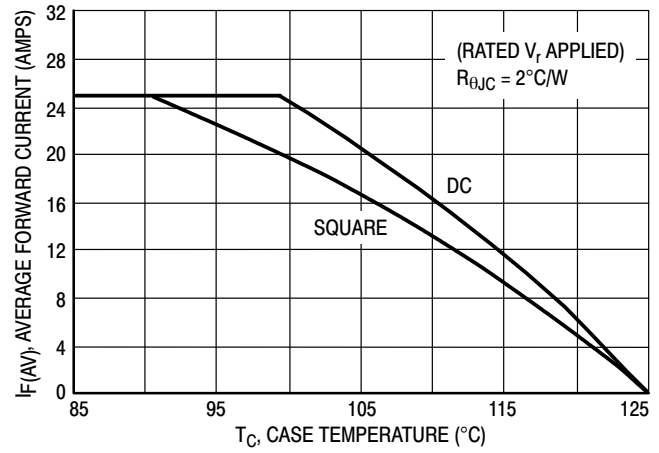


Figure 4. Current Derating, Case

# MECHANICAL CASE OUTLINE

## PACKAGE DIMENSIONS

ON Semiconductor®



**D<sup>2</sup>PAK 3**  
CASE 418B-04  
ISSUE L

DATE 17 FEB 2015

SCALE 1:1

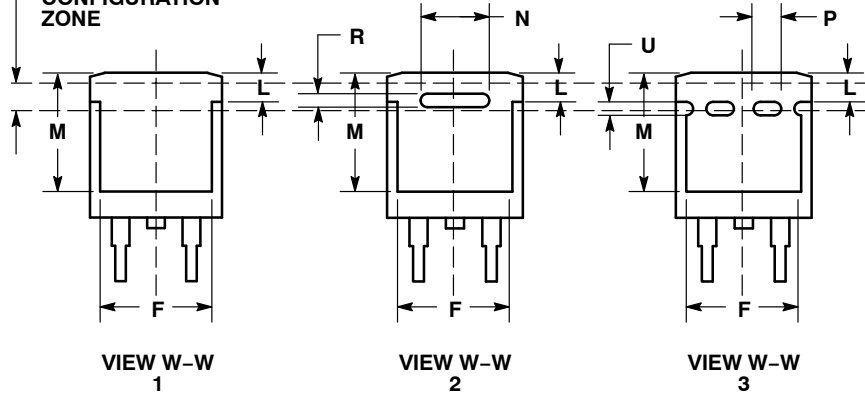


**NOTES:**

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. 418B-01 THRU 418B-03 OBSOLETE, NEW STANDARD 418B-04.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.340	0.380	8.64	9.65
B	0.380	0.405	9.65	10.29
C	0.160	0.190	4.06	4.83
D	0.020	0.035	0.51	0.89
E	0.045	0.055	1.14	1.40
F	0.310	0.350	7.87	8.89
G	0.100	BSC	2.54	BSC
H	0.080	0.110	2.03	2.79
J	0.018	0.025	0.46	0.64
K	0.090	0.110	2.29	2.79
L	0.052	0.072	1.32	1.83
M	0.280	0.320	7.11	8.13
N	0.197	REF	5.00	REF
P	0.079	REF	2.00	REF
R	0.039	REF	0.99	REF
S	0.575	0.625	14.60	15.88
V	0.045	0.055	1.14	1.40

**VARIABLE CONFIGURATION ZONE**



- |  |   |   |  |   |  |
|--|---|---|--|---|--|
| <b>STYLE 1:</b><br>PIN 1. BASE<br>2. COLLECTOR<br>3. EMITTER<br>4. COLLECTOR | <b>STYLE 2:</b><br>PIN 1. GATE<br>2. DRAIN<br>3. SOURCE<br>4. DRAIN | <b>STYLE 3:</b><br>PIN 1. ANODE<br>2. CATHODE<br>3. ANODE<br>4. CATHODE | <b>STYLE 4:</b><br>PIN 1. GATE<br>2. COLLECTOR<br>3. EMITTER<br>4. COLLECTOR | <b>STYLE 5:</b><br>PIN 1. CATHODE<br>2. ANODE<br>3. CATHODE<br>4. ANODE | <b>STYLE 6:</b><br>PIN 1. NO CONNECT<br>2. CATHODE<br>3. ANODE<br>4. CATHODE |
|--|---|---|--|---|--|

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**D<sup>2</sup>PAK 3**  
CASE 418B-04  
ISSUE L

DATE 17 FEB 2015

**GENERIC  
MARKING DIAGRAM\***



- xx = Specific Device Code
- A = Assembly Location
- WL = Wafer Lot
- Y = Year
- WW = Work Week
- G = Pb-Free Package
- AKA = Polarity Indicator

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present.

**SOLDERING FOOTPRINT\***



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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